ABSTRACT

It is an object of the present invention to form a TFT which is required to have a high withstanding voltage ~~high pressure resistant~~ characteristic as well as to lower an off-current , a TFT which is required to have a high withstanding voltage ~~high pressure resistant~~ characteristic as well as to raise an on-current, and a TFT in which a short channel structure and the decline in the threshold voltage arising therefrom are attached importance to, on one and the same substrate. A TFT having gate insulating films with different thickness can be formed on one and the same substrate by providing auxiliary electrodes in addition to the gate electrodes over a semiconductor film as well as laminating the insulating films.